

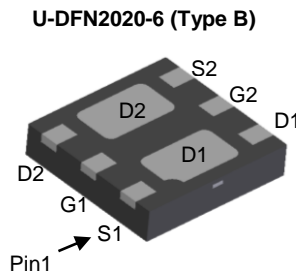
Product Summary

BV _{bss}	R _{DS(ON)} Max	I _D MAX T _A = +25°C
-20V	75mΩ @ V _{GS} = -4.5V	-3.2A
	110mΩ @ V _{GS} = -2.5V	-2.9A

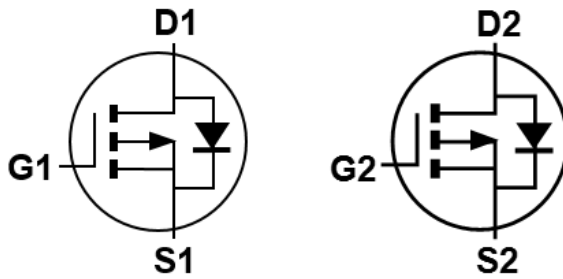
Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

- Load Switch
- Power Management Functions
- Portable Power Adaptors



Bottom View



Internal Schematic

Features

- PCB Footprint of 4mm²
- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Maximum Height
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

Mechanical Data

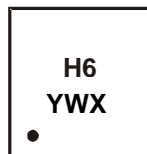
- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2110UFDB-7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMP2110UFDB-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



H6 = Product Type Marking Code
 YWX = Date Code Marking
 Y = Year (ex: 0 = 2020)
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)
 X = Internal Code (ex: U = Monday)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	9	0	1	2	3	4	5	6	7	8	9	0

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	T	U	V	W	X	Y	Z

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	-20	V	
Gate-Source Voltage	V_{GSS}	± 12	V	
Continuous Drain Current (Note 6) $V_{GS} = -4.5\text{V}$	I_D	$T_A = +25^\circ\text{C}$	-3.2	A
		$T_A = +70^\circ\text{C}$	-2.6	
Maximum Continuous Body Diode Forward Current (Note 6)	I_S	-1.05	A	
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	-15	A	

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	0.82	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	153	$^\circ\text{C}/\text{W}$
Total Power Dissipation (Note 6)	P_D	1.14	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	110	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	—	—	-1.0	μA	$V_{DS} = -16\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	μA	$V_{GS} = \pm 8\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.45	—	-1.0	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	—	75	m Ω	$V_{GS} = -4.5\text{V}, I_D = -2.8\text{A}$
		—	—	110		$V_{GS} = -2.5\text{V}, I_D = -2.0\text{A}$
		—	—	168		$V_{GS} = -1.8\text{V}, I_D = -1.0\text{A}$
Diode Forward Voltage	V_{SD}	—	—	-1.0	V	$V_{GS} = 0\text{V}, I_S = -1.0\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	443	—	pF	$V_{DS} = -10\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	59	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	47	—	pF	
Gate Resistance	R_g	—	8.5	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = -4.5\text{V}$)	Q_g	—	6.0	—	nC	$V_{DS} = -4.5\text{V}, I_D = -3.0\text{A}$
Total Gate Charge ($V_{GS} = -8\text{V}$)		—	12.7	—	nC	
Gate-Source Charge	Q_{gs}	—	0.6	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.8	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	4.0	—	ns	$V_{DS} = -10\text{V}, V_{GS} = -4.5\text{V}, R_L = 10\Omega, R_g = 6\Omega$
Turn-On Rise Time	t_R	—	3.7	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	24.5	—	ns	
Turn-Off Fall Time	t_F	—	9.5	—	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	8.3	—	ns	$I_S = -1.0\text{A}, dI/dt = 100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	Q_{RR}	—	2.0	—	nC	$I_S = -1.0\text{A}, dI/dt = 100\text{A}/\mu\text{s}$

- Notes:
- Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

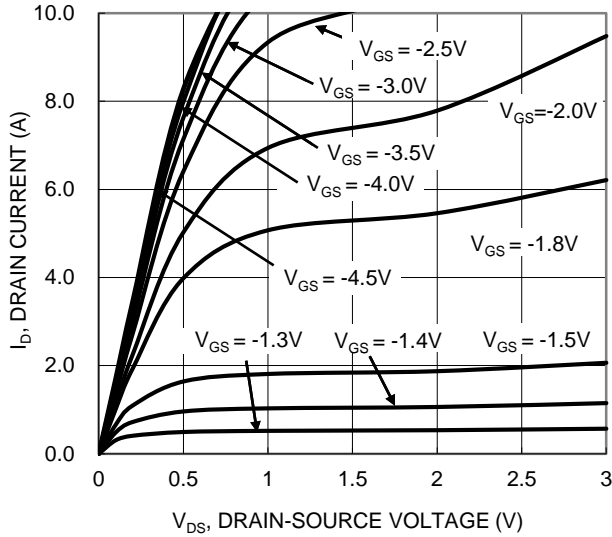


Figure 1. Typical Output Characteristic

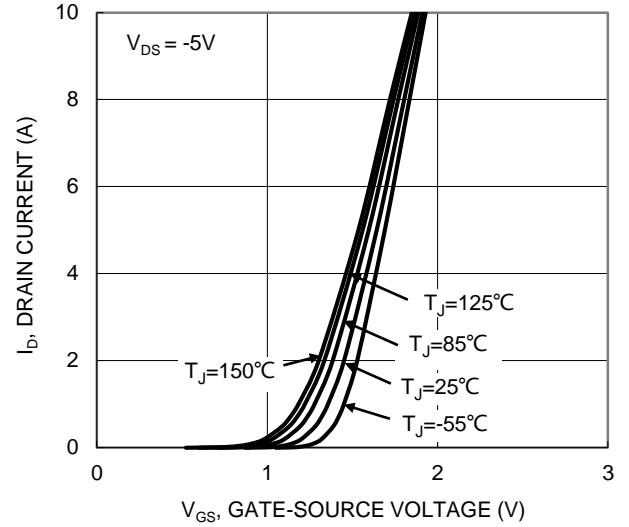


Figure 2. Typical Transfer Characteristic

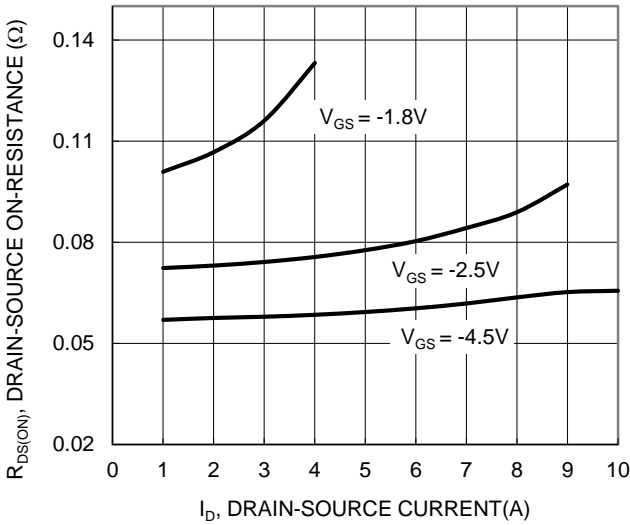


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

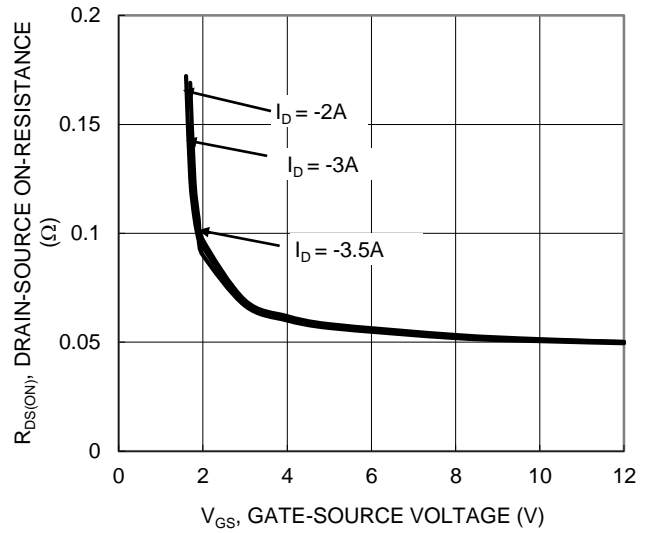


Figure 4. Typical Transfer Characteristic

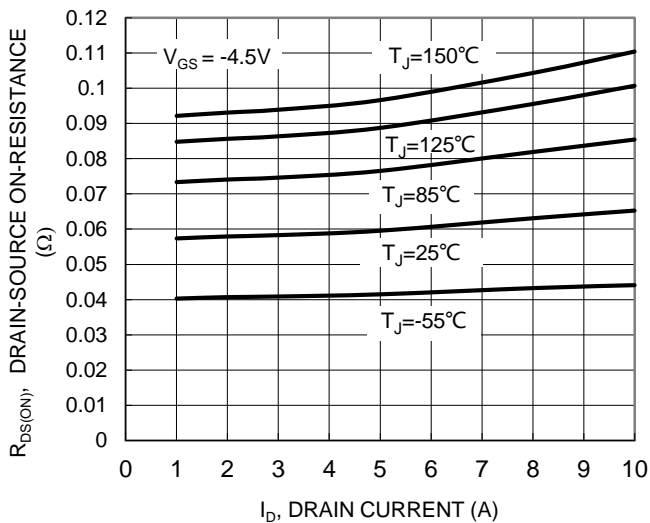


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

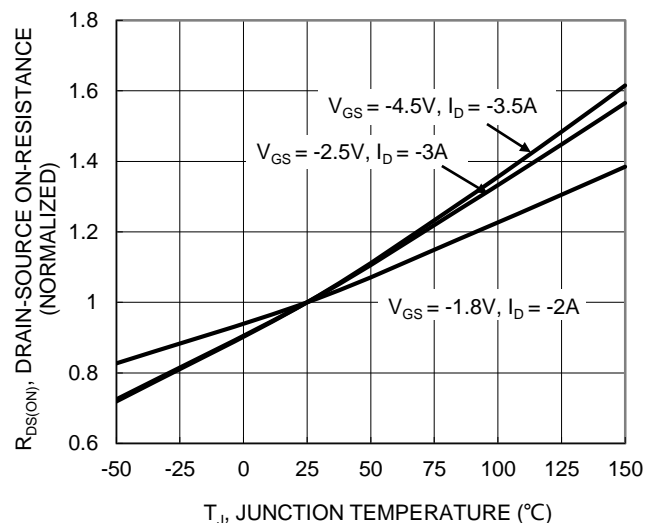
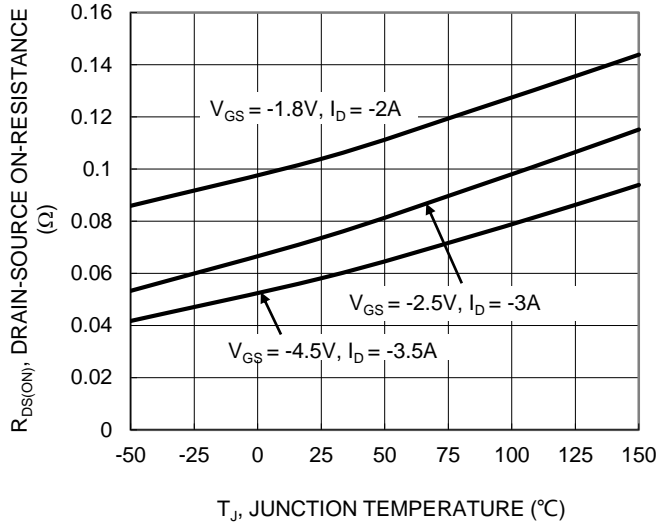
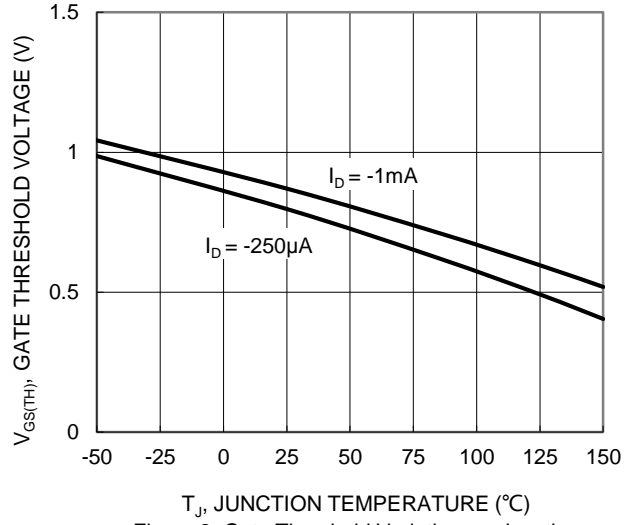


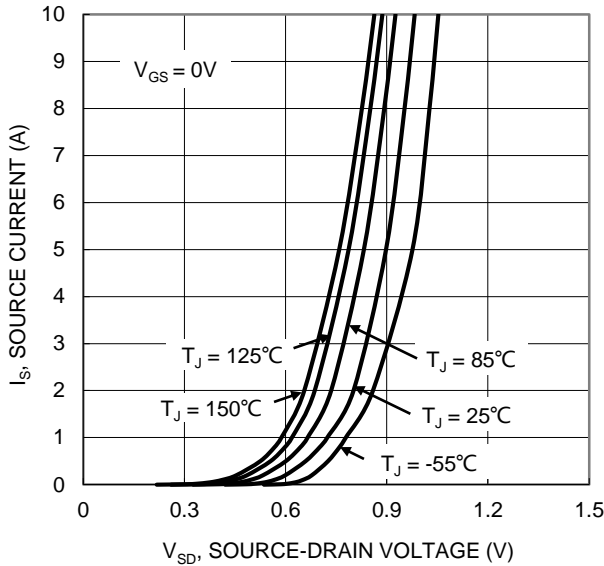
Figure 6. On-Resistance Variation with Junction Temperature



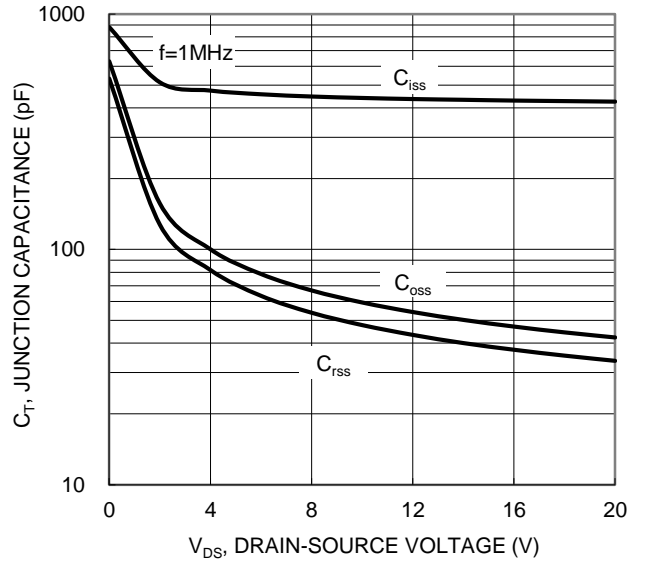
T_J, JUNCTION TEMPERATURE (°C)
Figure 7. On-Resistance Variation with Junction Temperature



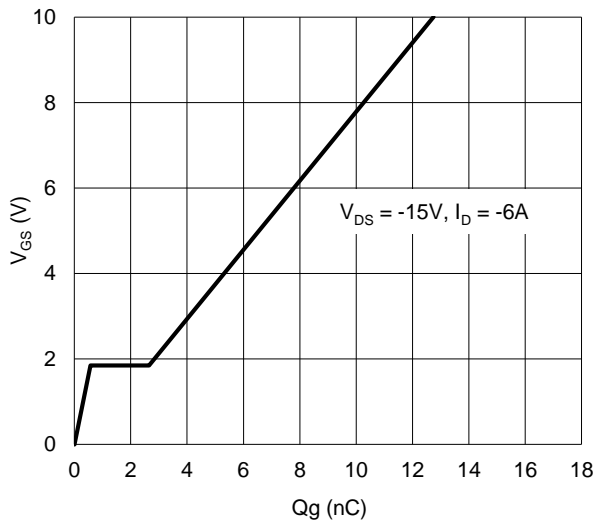
T_J, JUNCTION TEMPERATURE (°C)
Figure 8. Gate Threshold Variation vs. Junction Temperature



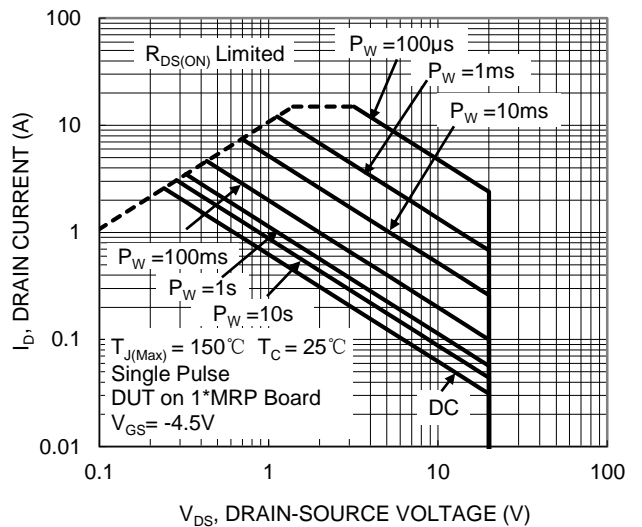
V_{SD}, SOURCE-DRAIN VOLTAGE (V)
Figure 9. Diode Forward Voltage vs. Current



V_{DS}, DRAIN-SOURCE VOLTAGE (V)
Figure 10. Typical Junction Capacitance



Qg (nC)
Figure 11. Gate Charge



V_{DS}, DRAIN-SOURCE VOLTAGE (V)
Figure 12. SOA, Safe Operation Area

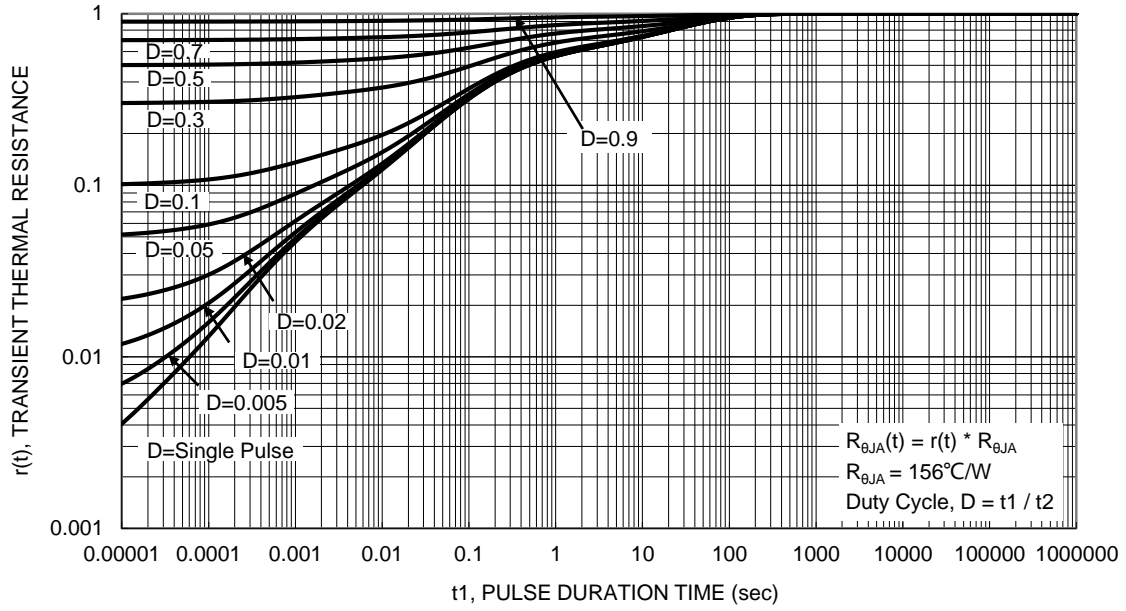


Figure 13. Transient Thermal Resistance

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